

To all our customers

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Renesas Technology Corp.  
Customer Support Dept.  
April 1, 2003

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# HZU Series

Silicon Epitaxial Planar Zener Diodes for Stabilizer

**RENESAS**

ADE-208-024G (Z)

Rev.7  
Dec. 2002

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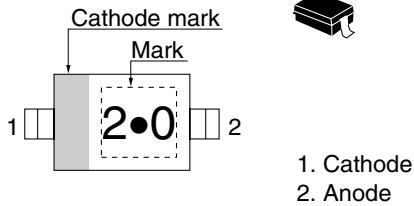
## Features

- Ultra small Resin Package (URP) is suitable for surface mount design.
- These diodes are delivered taped.

## Ordering Information

Type No.	Mark	Package Code
HZU Series	Let to Mark Code	URP

## Pin Arrangement



# HZU Series

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd *1	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. With P.C. Board.

## Electrical Characteristics

(Ta = 25°C)

Type	Grade	Zener Voltage		Reverse Current		Dynamic Resistance		
		V <sub>z</sub> (V) *1		Test Condition	I <sub>R</sub> (μA)	Test Condition	r <sub>d</sub> (Ω)	Test Condition
		Min	Max	I <sub>z</sub> (mA)	Max	V <sub>R</sub> (V)	Max	I <sub>z</sub> (mA)
HZU2.0	B	1.90	2.20	5	120	0.5	100	5
HZU2.2	B	2.10	2.40	5	120	0.7	100	5
HZU2.4	B	2.30	2.60	5	120	1.0	100	5
HZU2.7	B	2.50	2.90	5	120	1.0	110	5
	B1	2.50	2.75					
	B2	2.65	2.90					
HZU3.0	B	2.80	3.20	5	50	1.0	120	5
	B1	2.80	3.05					
	B2	2.95	3.20					
HZU3.3	B	3.10	3.50	5	20	1.0	130	5
	B1	3.10	3.35					
	B2	3.25	3.50					
HZU3.6	B	3.40	3.80	5	10	1.0	130	5
	B1	3.40	3.65					
	B2	3.55	3.80					
HZU3.9	B	3.70	4.10	5	10	1.0	130	5
	B1	3.70	3.97					
	B2	3.87	4.10					

Note: 1. Tested with pulse (P<sub>w</sub> = 40 ms).

Type	Grade	Zener Voltage		Reverse Current		Dynamic Resistance		
		$V_z$ (V) *1		Test Condition	$I_R$ ( $\mu$ A)	Test Condition	$r_d$ ( $\Omega$ )	Test Condition
		Min	Max	$I_z$ (mA)	Max	$V_R$ (V)	Max	$I_z$ (mA)
HZU4.3	B	4.01	4.48	5	10	1.0	130	5
	B1	4.01	4.21					
	B2	4.15	4.34					
	B3	4.28	4.48					
HZU4.7	B	4.42	4.90	5	10	1.0	130	5
	B1	4.42	4.61					
	B2	4.55	4.75					
	B3	4.69	4.90					
HZU5.1	B	4.84	5.37	5	5	1.5	130	5
	B1	4.84	5.04					
	B2	4.98	5.20					
	B3	5.14	5.37					
HZU5.6	B	5.31	5.92	5	5	2.5	80	5
	B1	5.31	5.55					
	B2	5.49	5.73					
	B3	5.67	5.92					
HZU6.2	B	5.86	6.53	5	2	3.0	50	5
	B1	5.86	6.12					
	B2	6.06	6.33					
	B3	6.26	6.53					
HZU6.8	B	6.47	7.14	5	2	3.5	30	5
	B1	6.47	6.73					
	B2	6.65	6.93					
	B3	6.86	7.14					
HZU7.5	B	7.06	7.84	5	2	4.0	30	5
	B1	7.06	7.36					
	B2	7.28	7.60					
	B3	7.52	7.84					
HZU8.2	B	7.76	8.64	5	2	5.0	30	5
	B1	7.76	8.10					
	B2	8.02	8.36					
	B3	8.28	8.64					

Note: 1. Tested with pulse ( $P_w = 40$  ms).

# HZU Series

Type	Grade	Zener Voltage		Reverse Current		Dynamic Resistance		
		$V_z$ (V) *1		Test Condition	$I_R$ ( $\mu$ A)	Test Condition	$r_d$ ( $\Omega$ )	Test Condition
		Min	Max	$I_z$ (mA)	Max	$V_R$ (V)	Max	$I_z$ (mA)
HZU9.1	B	8.56	9.55	5	2	6.0	30	5
	B1	8.56	8.93					
	B2	8.85	9.23					
	B3	9.15	9.55					
HZU10	B	9.45	10.55	5	2	7.0	30	5
	B1	9.45	9.87					
	B2	9.77	10.21					
	B3	10.11	10.55					
HZU11	B	10.44	11.56	5	2	8.0	30	5
	B1	10.44	10.88					
	B2	10.76	11.22					
	B3	11.10	11.56					
HZU12	B	11.42	12.60	5	2	9.0	35	5
	B1	11.42	11.90					
	B2	11.74	12.24					
	B3	12.08	12.60					
HZU13	B	12.47	13.96	5	2	10.0	35	5
	B1	12.47	13.03					
	B2	12.91	13.49					
	B3	13.37	13.96					
HZU15	B	13.84	15.52	5	2	11.0	40	5
	B1	13.84	14.46					
	B2	14.34	14.98					
	B3	14.85	15.52					
HZU16	B	15.37	17.09	5	2	12.0	40	5
	B1	15.37	16.01					
	B2	15.58	16.51					
	B3	16.35	17.09					
HZU18	B	16.94	19.03	5	2	13.0	45	5
	B1	16.94	17.70					
	B2	17.56	18.35					
	B3	18.21	19.03					

Note: 1. Tested with pulse ( $P_w = 40$  ms).

Type	Grade	Zener Voltage		Reverse Current		Dynamic Resistance		
		$V_z$ (V) * <sup>1</sup>		Test Condition	$I_R$ ( $\mu$ A)	Test Condition	$r_d$ ( $\Omega$ )	Test Condition
		Min	Max	$I_z$ (mA)	Max	$V_R$ (V)	Max	$I_z$ (mA)
HZU20	B	18.86	21.08	5	2	15.0	50	5
	B1	18.86	19.70					
	B2	19.52	20.39					
	B3	20.21	21.08					
HZU22	B	20.88	23.17	5	2	17.0	55	5
	B1	20.88	21.77					
	B2	21.54	22.47					
	B3	22.23	23.17					
HZU24	B	22.93	25.57	5	2	19.0	60	5
	B1	22.93	23.96					
	B2	23.72	24.78					
	B3	24.54	25.57					
HZU27	B	25.10	28.90	2	2	21.0	70	2
HZU30	B	28.00	32.00	2	2	23.0	80	2
HZU33	B	31.00	35.00	2	2	25.0	80	2
HZU36	B	34.00	38.00	2	2	27.0	90	2

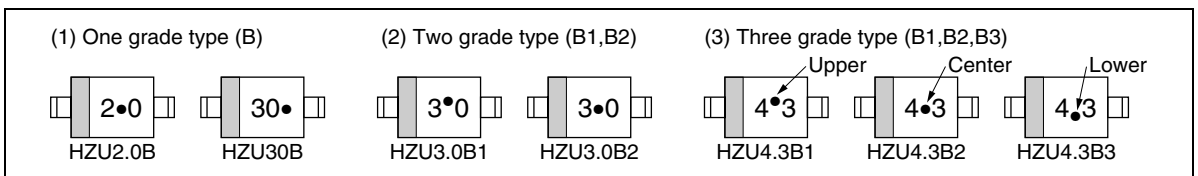
Note: 1. Tested with pulse ( $P_w = 40$  ms).

# HZU Series

## Mark Code

Type	Grade	Mark No.	Type	Grade	Mark No.	Type	Grade	Mark No.
HZU2.0	B	2•0	HZU6.2	B1	6•2	HZU13	B1	13•
HZU2.2	B	2•2		B2	6•2		B2	13•
HZU2.4	B	2•4		B3	6•2		B3	13•
HZU2.7	B1	2•7	HZU6.8	B1	6•8	HZU15	B1	15•
	B2	2•7		B2	6•8		B2	15•
HZU3.0	B1	3•0		B3	6•8		B3	15•
	B2	3•0	HZU7.5	B1	7•5	HZU16	B1	16•
HZU3.3	B1	3•3		B2	7•5		B2	16•
	B2	3•3		B3	7•5		B3	16•
HZU3.6	B1	3•6	HZU8.2	B1	8•2	HZU18	B1	18•
	B2	3•6		B2	8•2		B2	18•
HZU3.9	B1	3•9		B3	8•2		B3	18•
	B2	3•9	HZU9.1	B1	9•1	HZU20	B1	20•
HZU4.3	B1	4•3		B2	9•1		B2	20•
	B2	4•3		B3	9•1		B3	20•
	B3	4•3	HZU10	B1	10•	HZU22	B1	22•
HZU4.7	B1	4•7		B2	10•		B2	22•
	B2	4•7		B3	10•		B3	22•
	B3	4•7	HZU11	B1	11•	HZU24	B1	24•
HZU5.1	B1	5•1		B2	11•		B2	24•
	B2	5•1		B3	11•		B3	24•
	B3	5•1	HZU12	B1	12•	HZU27	B	27•
HZU5.6	B1	5•6		B2	12•	HZU30	B	30•
	B2	5•6		B3	12•	HZU33	B	33•
	B3	5•6				HZU36	B	36•

Notes: 1. Example of Marking



2. The grade B type includes from B1 min. to B3 (or B2) max.
3. B grade is standard and has better delivery, These are marked one of B1, B2, B3.
4. Type No. is as follows; HZU2.0B, HZU2.2B, ... HZU36B. (B grade)
5. Type No. is as follows; HZU2.7B1, HZU2.7B2, ... HZU24B3. (B 1, B2, B3 grade)



Main Characteristic

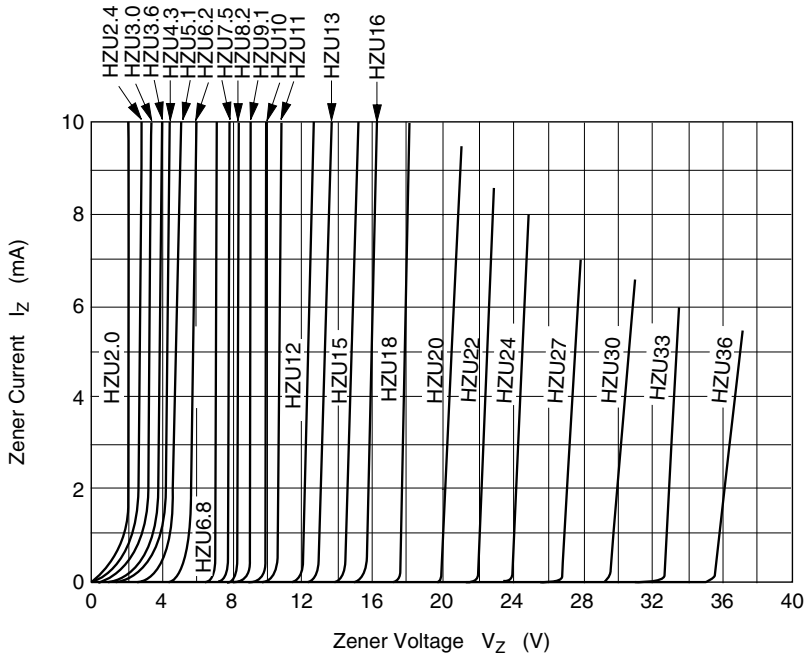


Fig.1 Zener current vs. Zener voltage

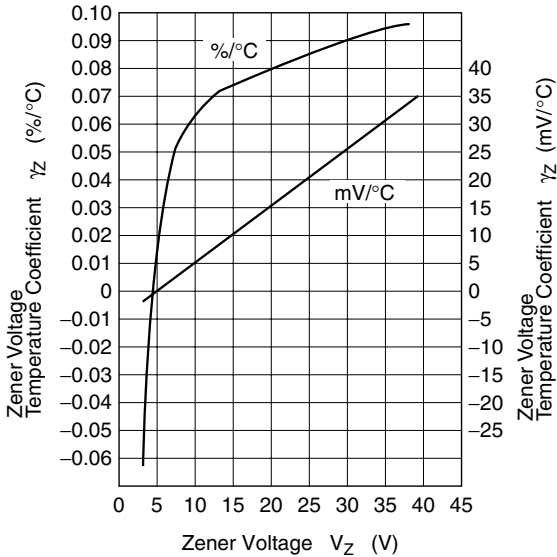


Fig.2 Temperature Coefficient vs. Zener voltage

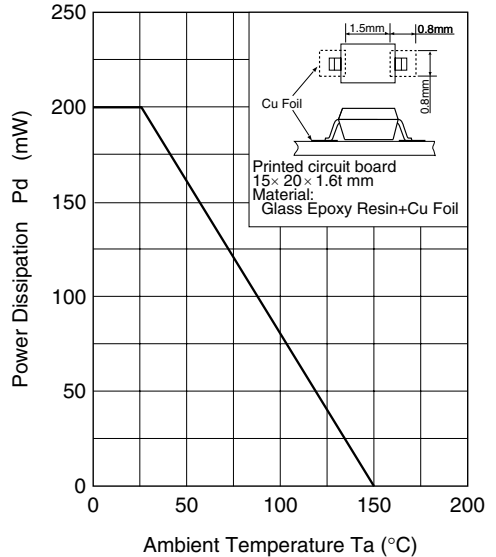
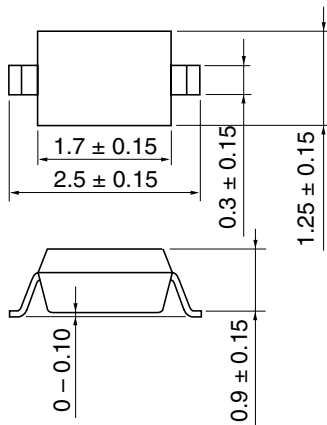


Fig.3 Power Dissipation vs. Ambient Temperature

## Package Dimensions

As of July, 2002

Unit: mm



Hitachi Code	URP
JEDEC	Conforms
JEITA	—
Mass (reference value)	0.004 g

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# HITACHI

**Hitachi, Ltd.**

Semiconductor & Integrated Circuits  
 Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan  
 Tel: (03) 3270-2111 Fax: (03) 3270-5109

URL <http://www.hitachisemiconductor.com/>

**For further information write to:**

<p>Hitachi Semiconductor (America) Inc.                  179 East Tasman Drive                  San Jose, CA 95134                  Tel: &lt;1&gt; (408) 433-1990                  Fax: &lt;1&gt; (408) 433-0223</p>	<p>Hitachi Europe Ltd.                  Electronic Components Group                  Whitebrook Park                  Lower Cookham Road                  Maidenhead                  Berkshire SL6 8YA, United Kingdom                  Tel: &lt;44&gt; (1628) 585000                  Fax: &lt;44&gt; (1628) 778322</p>	<p>Hitachi Asia Ltd.                  Hitachi Tower                  16 Collyer Quay #20-00                  Singapore 049318                  Tel : &lt;65&gt;-6538-6533/6538-8577                  Fax : &lt;65&gt;-6538-6933/6538-3877                  URL : <a href="http://semiconductor.hitachi.com.sg">http://semiconductor.hitachi.com.sg</a></p>	<p>Hitachi Asia (Hong Kong) Ltd.                  Group III (Electronic Components)                  7/F., North Tower                  World Finance Centre,                  Harbour City, Canton Road                  Tsim Sha Tsui, Kowloon Hong Kong                  Tel : &lt;852&gt;-2735-9218                  Fax : &lt;852&gt;-2730-0281                  URL : <a href="http://semiconductor.hitachi.com.hk">http://semiconductor.hitachi.com.hk</a></p>
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